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This index covers all technical items—papers, correspondence, reviews, etc.—that appeared in this periodical during 2021, and items from previous years that were commented upon or corrected in 2021. Departments and other items may also be covered if they have been judged to have archival value.

The Author Index contains the primary entry for each item, listed under the first author's name. The primary entry includes the coauthors' names, the title of the paper or other item, and its location, specified by the publication abbreviation, year, month, and inclusive pagination. The Subject Index contains entries describing the item under all appropriate subject headings, plus the first author's name, the publication abbreviation, month, and year, and inclusive pages. Note that the item title is found only under the primary entry in the Author Index.

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Field effect transistor switches

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Plasma switches

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